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Substitute for form 1449A/PTO	C	Index the Peparwork Raduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid GMB control number. Complete If Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	per 09/945,507	
(Use as many sheets as necessary)	Filing Date	August 30, 2001	
0.	First Named Inver	ntor Forbes, Leonard	
	Group Art Unit	2824	
SEP	Examiner Name	Dinh, Son	
Sheet 1 of 2	Attorney Docket	No: 1303.014US1	

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	Filing Date	August 30, 2001	
	First Named Inventor	Forbes, Leonard	
	Group Art Unit	2824	
	Examiner Name	Dinh, Son	
Sheet 2 of 2	Attorney Docket No: 1303.014US1		

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